

### **General Description**

The WSR70P10D is the highest performance trench P-Ch MOSFET with extreme high cell density , which provide excellent  $R_{\text{DSON}}$  and gate charge for most of the small power switching and load switch applications.

The WSR70P10D meet the RoHS and Green Product requirement with full function reliability approved.

#### **Features**

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent Cdv/dt effect decline
- Green Device Available

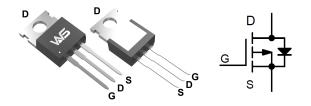
### **Product Summery**

BV <sub>DSS</sub>	R <sub>DSON</sub>	I <sub>D</sub>
-100V	19mΩ	-70A

### **Applications**

Inverters

### **TO-220AB Pin Configuration**



### **Absolute Maximum Ratings**

Symbol	Parameter	Rating	Unit							
Common Ratings (T <sub>C</sub> =25°C Unless Otherwise Noted)										
V <sub>DSS</sub>	Drain-Source Voltage	-100	V							
$V_{GSS}$	Gate-Source Voltage	±25								
TJ	Maximum Junction Temperature	175	°C							
T <sub>STG</sub>	Storage Temperature Range	-55 to 175	°C							
I <sub>S</sub>	Diode Continuous Forward Current	T <sub>C</sub> =25°C	-70	Α						
Mounted or	Mounted on Large Heat Sink									
I <sub>DP</sub> ①	300μs Pulse Drain Current Tested	T <sub>C</sub> =25°C	-240	Α						
$I_D^{\textcircled{2}}$	T <sub>C</sub> =	T <sub>C</sub> =25°C	-70							
	Continuous Drain Current( $V_{GS}$ =-10V) $T_C$ =100°C		-45	Α						
$P_{D}$	Mayimum Dayyar Dissination	T <sub>C</sub> =25°C	190	W						
	Maximum Power Dissipation	T <sub>C</sub> =100°C	95							
$R_{ heta JC}$	Thermal Resistance-Junction to Case		0.8	°C/W						
$R_{\theta JA}$	Thermal Resistance-Junction to Ambient		62.5	°C/W						
Drain-Sour	ce Avalanche Ratings									
E <sub>AS</sub>	Avalanche Energy, Single Pulsed	400	mJ							



# **Electrical Characteristics** (T<sub>C</sub>=25°C Unless Otherwise Noted)

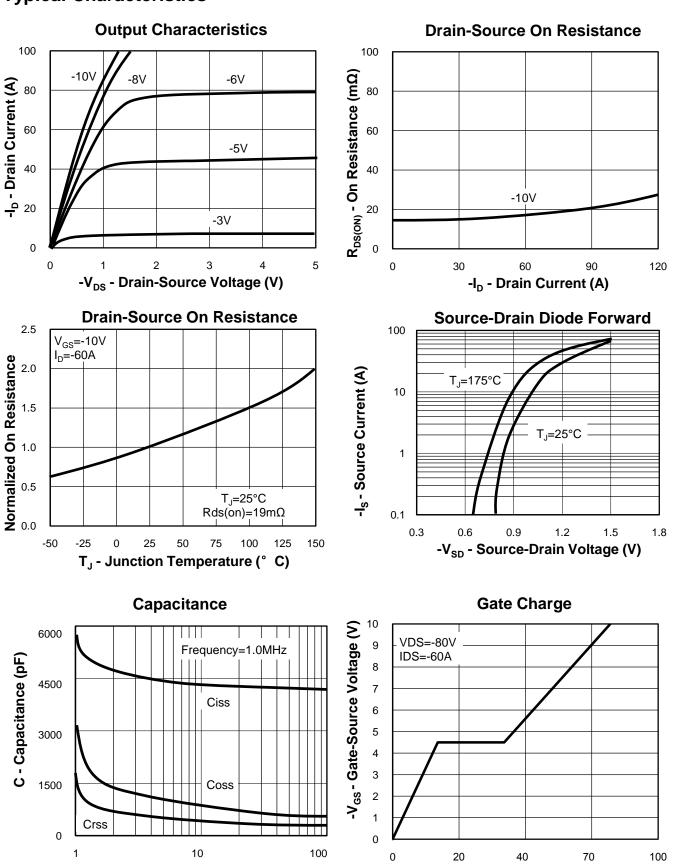
Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Unit
Static Cha	racteristics		•	•		
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>DS</sub> =-250μA	-100			V
	Zero Gate Voltage Drain Current	V <sub>DS</sub> =-100V, V <sub>GS</sub> =0V			-1	μΑ
I <sub>DSS</sub>		T <sub>J</sub> =125°C			-30	
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS}=V_{GS}$ , $I_{DS}=-250\mu A$	-1.2	-1.6	-2.5	V
I <sub>GSS</sub>	Gate Leakage Current	$V_{GS}$ =±25V, $V_{DS}$ =0V			±100	nA
R <sub>DS(ON)</sub>	Drain-Source On-state Resistance	V <sub>GS</sub> =-10V, I <sub>DS</sub> =-20A		19	25	mΩ
Diode Cha	racteristics			•		
V <sub>SD</sub>	Diode Forward Voltage	I <sub>SD</sub> =-30A, V <sub>GS</sub> =0V			-1.2	V
trr	Reverse Recovery Time	FA -11 /-14 400A/		208		ns
Qrr	Reverse Recovery Charge	Isp=-5A, dlsp/dt=100A/µs		560		nC
Dynamic C	Characteristics <sup>©</sup>			•		
R <sub>G</sub>	Gate Resistance	V <sub>GS</sub> =0V,V <sub>DS</sub> =0V,F=1MHz		2		Ω
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V,		4230		pF
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> =-50V, Frequency=1.0MHz		388		
C <sub>rss</sub>	Reverse Transfer Capacitance			26		
t <sub>d(ON)</sub>	Turn-on Delay Time			26		ns
t <sub>r</sub>	Turn-on Rise Time	V <sub>DD</sub> =-50V,I <sub>DS</sub> =-5A,		78		
t <sub>d(OFF)</sub>	Turn-off Delay Time	$V_{GEN}$ =-10 $V$ , $R_G$ =6 $\Omega$		200		
t <sub>f</sub>	Turn-off Fall Time			210		
Gate Char	ge Characteristics <sup>⑤</sup>					
Q <sub>g</sub>	Total Gate Charge			80		nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>DS</sub> =-50V, V <sub>GS</sub> =-10V, I <sub>DS</sub> =-5A		15.6		
$Q_{gd}$	Gate-Drain Charge			17.2		
		I.				

Notes:

- ①Pulse width limited by safe operating area.
- ②Calculated continuous current based on maximum allowable junction temperature.
- ③Limited by  $T_{Jmax}$ ,  $I_{AS}$  =-40A,  $V_{DD}$  =-60V,  $R_{G}$  = 50Ω, Starting  $T_{J}$  = 25° C.
- ④Pulse test;Pulse width≤300µs, duty cycle≤2%.
- ⑤Guaranteed by design, not subject to production testing.



## **Typical Characteristics**

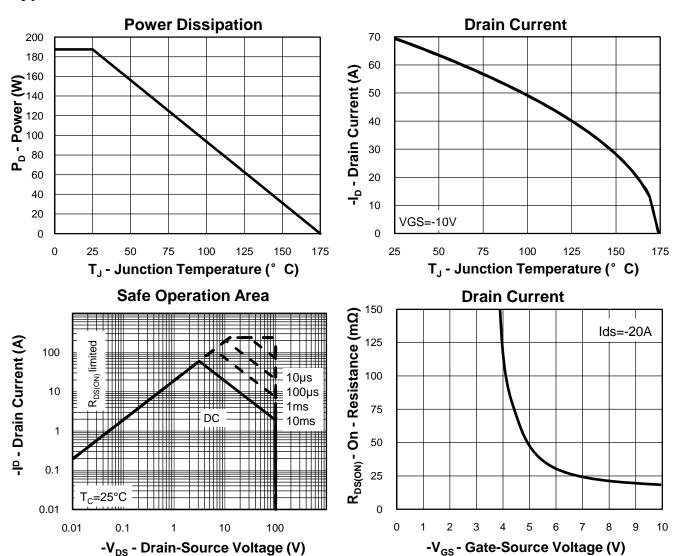


Q<sub>G</sub> - Gate Charge (nC)

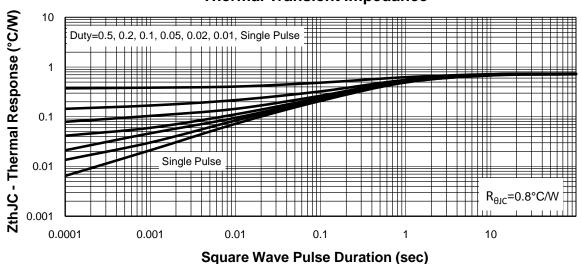
-V<sub>DS</sub> - Drain-Source Voltage (V)



## **Typical Characteristics**



### **Thermal Transient Impedance**





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